

# RJF0609JSP

60V - 1.5V Silicon N Channel Thermal FET Power Switching R07DS1066EJ0200 Rev.2.00 Jan 15, 2016

Datasheet

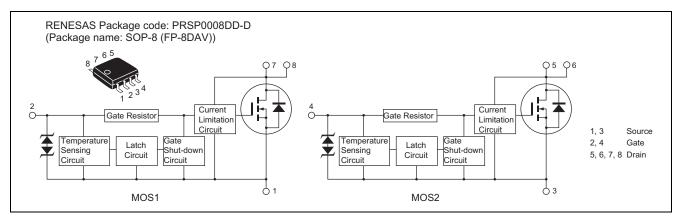
### Description

This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

#### Features

- Logic level operation (4 V Gate drive).
- Built-in the over temperature shut-down circuit.
- High endurance capability against to the short circuit.
- Latch type shut down operation (need 0 voltage recovery).
- Built-in the current limitation circuit.
- High density mounting
- Power supply voltage applies 12 V and 24 V.
- AEC-Q101 Compliant

#### Outline



#### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ Unit ltem Symbol Ratings Drain to source voltage VDSS 60 V Gate to source voltage VGSS 16 V Gate to source voltage VGSS V -2.5 D Note4 Drain current 1.5 А Body-drain diode reverse drain current IDR 1.5 A IAP Note 3 Avalanche current 1.5 A EAR Note 3 Avalanche energy m.J 9.6 Pch Note 1 Channel dissipation W 1 Pch Note 2 Channel dissipation 1.5 W Channel temperature Tch °C 150 °C Storage temperature Tstg -55 to +150

Notes: 1. 1 Drive operation : When using the glass epoxy board (FR4  $40 \times 40 \times 1.6$  mm), PW  $\leq 10$  s

2. 2 Drive operation : When using the glass epoxy board (FR4 40  $\times$  40  $\times$  1.6 mm), PW  $\leq$  10 s

3. Tch = 25°C, Rg  $\geq$  50  $\Omega$ 

4. It provides by the current limitation lower bound value.



### **Typical Operation Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	VIH	3.5			V	
	VIL	_		1.2	V	
Input current	IIH1			100	μA	Vi = 8 V, V <sub>DS</sub> = 0
(Gate non shut down)	I <sub>IH2</sub>			50	μA	Vi = 3.5 V, V <sub>DS</sub> = 0
	١L			1	μA	Vi = 1.2 V, V <sub>DS</sub> = 0
Input current	I <sub>IH(sd)1</sub>		0.8		mA	Vi = 8 V, V <sub>DS</sub> = 0
(Gate shut down)	I <sub>IH(sd)2</sub>	_	0.35		mA	$Vi = 3.5 V, V_{DS} = 0$
Shut down temperature	Tsd		175		°C	Channel temperature
Gate operation voltage	Vop	3.5		12	V	
Drain current (Current limitation value)	I <sub>D limt</sub>	1.5			A	$V_{GS}$ = 5 V, $V_{DS}$ = 10 V <sup>Note 5</sup>

Notes: 5. Pulse test

#### **Electrical Characteristics**

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain current				5.4	A	$V_{GS} = 3.5 \text{ V}, \text{ V}_{DS} = 10 \text{ V}^{\text{Note 6}}$
				10	mA	$V_{GS} = 3.3 V, V_{DS} = 10 V$ $V_{GS} = 1.2 V, V_{DS} = 10 V$
	ID2 ID3	1.5			A	$V_{GS} = 1.2 V, V_{DS} = 10 V$ $V_{GS} = 12 V, V_{DS} = 10 V^{Note 6}$
Drain to source breakdown	V <sub>(BR)DSS</sub>	60			X V	$V_{GS} = 12 \text{ V}, \text{ V}_{DS} = 10 \text{ V}$ $I_D = 10 \text{ mA}, \text{ V}_{GS} = 0$
voltage	V (BR)D55	00			v	$\mathbf{U} = 10 \mathbf{m} \mathbf{A}, \mathbf{VGS} = 0$
Gate to source breakdown	V <sub>(BR)GSS</sub>	16	_	_	V	$I_G = 800 \ \mu A, \ V_{DS} = 0$
voltage	V <sub>(BR)</sub> GSS	-2.5	_	—	V	$I_G = -100 \ \mu A, V_{DS} = 0$
Gate to source leak current	Igss1		_	100	μA	$V_{GS} = 8 V, V_{DS} = 0$
	Igss2		_	50	μA	$V_{GS} = 3.5 V, V_{DS} = 0$
	Igss3		—	1	μA	V <sub>GS</sub> = 1.2 V, V <sub>DS</sub> = 0
	Igss4		—	-100	μA	$V_{GS} = -2.4 \text{ V}, V_{DS} = 0$
Input current (shut down)	IGS(OP)1		0.8	—	mA	$V_{GS} = 8 V, V_{DS} = 0$
	IGS(OP)2		0.35	—	mA	$V_{GS} = 3.5 V, V_{DS} = 0$
Zero gate voltage drain current	IDSS		—	10	μΑ	$V_{DS} = 32 V, V_{GS} = 0$
						Ta = 125°C
Gate to source cutoff voltage	VGS(off)	1.1	_	2.1	V	$I_D = 1 \text{ mA}, V_{DS} = -0 \text{ V}$
Forward transfer admittance	y <sub>fs</sub>	1.0	2.2	—	S	$I_D = 0.75 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note 6}}$
Static drain to source on state	R <sub>DS(on)</sub>		208	350	mΩ	$I_D = 0.75 \text{ A}, V_{GS} = 4 \text{ V}^{\text{Note 6}}$
resistance	R <sub>DS(on)</sub>		142	263	mΩ	$I_D = 0.75 \text{ A}, V_{GS} = 10 \text{ V}^{Note 6}$
Output capacitance	Coss		265	_	pF	$V_{DS} = 10 V, V_{GS} = 0, f = 1MHz$
Turn-on delay time	t <sub>d(on)</sub>		0.55	_	μS	I <sub>D</sub> = 0.7 A, V <sub>GS</sub> = 10 V
Rise time	tr		1.88	_	μS	$R_L = 43 \Omega$
Turn-off delay time	t <sub>d(off)</sub>	_	3.9	—	μS	
Fall time	t <sub>f</sub>	_	3.7	—	μS	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.82	—	V	$I_F = 1.5 \text{ A}, \text{ V}_{GS} = 0$
Body-drain diode reverse	trr	_	71	—	ns	$I_F = 1.5 \text{ A}, V_{GS} = 0$
recovery time						di <sub>F</sub> /dt = 50 A/µs
Over load shut down	t <sub>os1</sub>	_	1.02		ms	$V_{GS} = 5 \text{ V}, V_{DD} = 16 \text{ V}$
operation time Note 7	t <sub>os2</sub>	_	0.59	_	ms	$V_{GS} = 5 V, V_{DD} = 24 V$

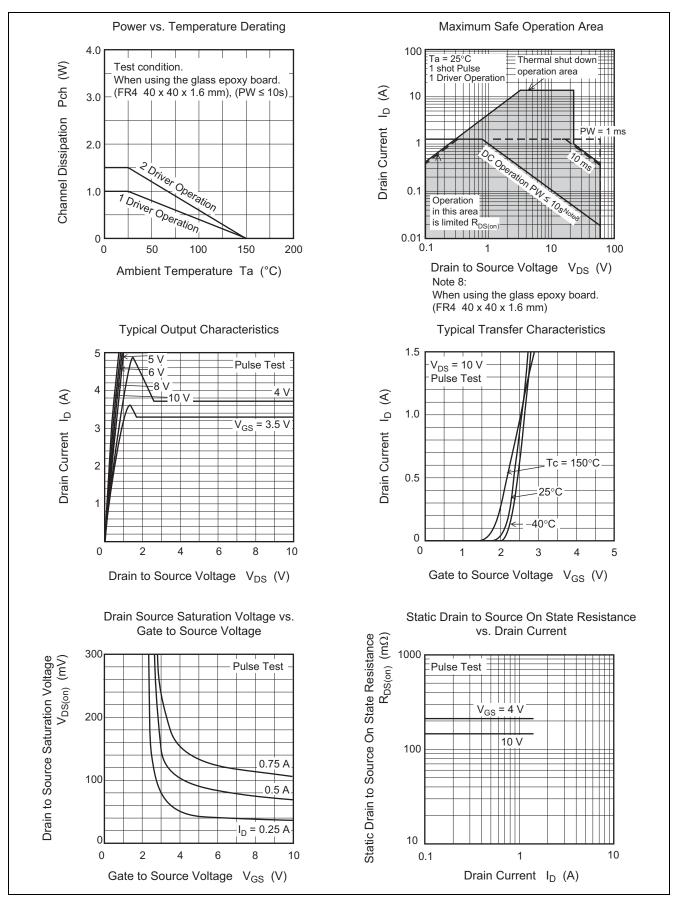
Notes: 6. Pulse test

7. Including the junction temperature rise of the over loaded condition.

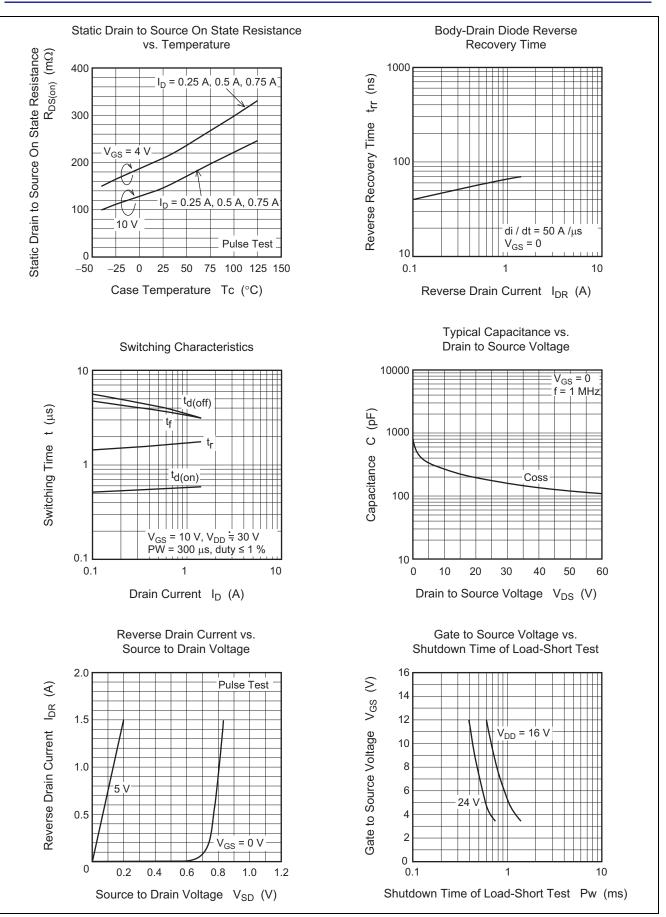
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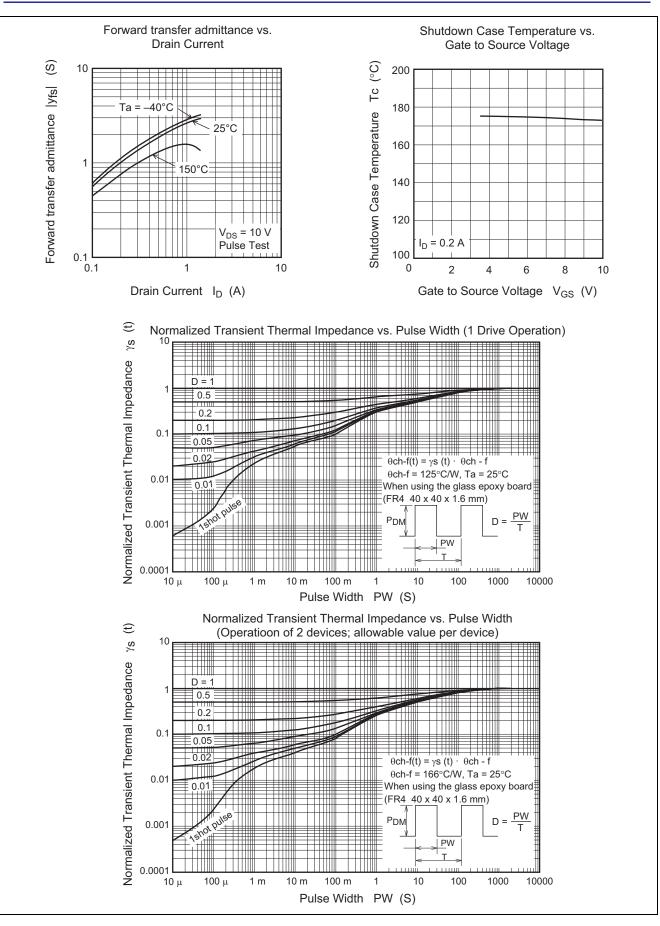
#### **Main Characteristics**

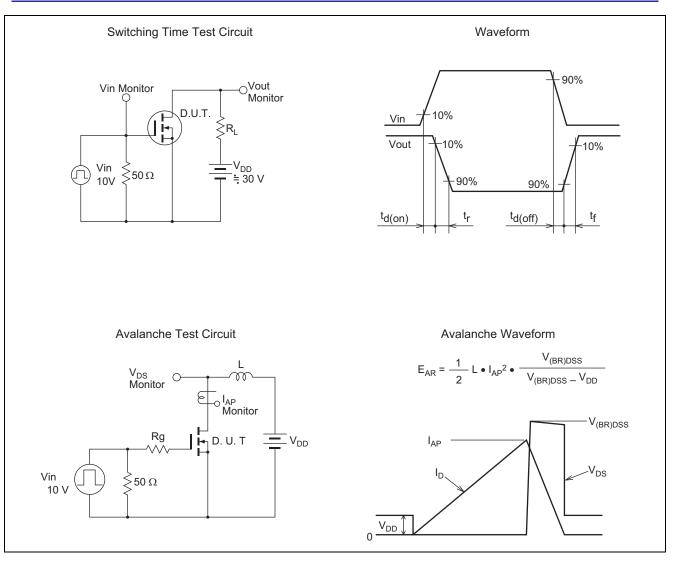






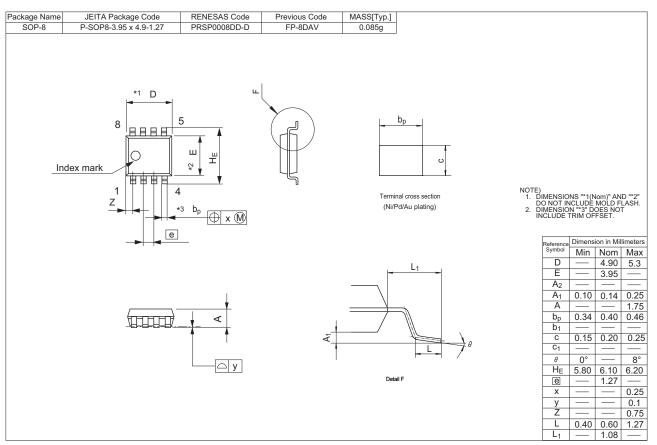








#### **Package Dimensions**



#### **Ordering Information**

Orderable Part Number	Quantity	Shipping Container		
RJF0609JSP-00-J0	2500 pcs/reel	Taping		

Note: The symbol of 2nd "-" is occasionally presented as "#".



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